



T-31-25

SD3300, SD3301

N-CHANNEL ENHANCEMENT-MODE D-MOS POWER FETs

ORDERING INFORMATION

Sorted Chips in Waffle Pack	SD3300CHP	SD3301CHP
TO-205AF (TO-39) Hermetic Package	SD3300HD	SD3301HD
TO-226AA (TO-92) Plastic Package	SD3300BD	SD3301BD
TO-237 (TO-92*) Plastic Package	SD3300AD	SD3301AD
Description	100V, 0.6 ohm	60V, 0.4 ohm

FEATURES

- Gate Stand-off Voltage, $\pm 40V$ min.
- Continuous I_D of 1 Amp in small package
- Wide Variety of Packages

APPLICATIONS

- Motor Controls
- Line Drivers
- Power Supplies

ABSOLUTE MAXIMUM RATINGS ($T_C = +25^\circ C$ unless otherwise noted)

Drain-Source Voltage	SD3300	100V
	SD3301	60V
Drain-Gate Voltage ($R_{GS} = 1M\Omega$)	SD3300	100V
	SD3301	60V
Gate-Source Voltage		$\pm 40V$
Continuous Drain Current		
	$T_C = +100^\circ C$	$T_C = +25^\circ C$
SD3300AD	1.2A	1.9A
SD3300BD	1.0A	1.6A
SD3300HD	2.25A	3.5A
SD3301AD	1.4A	2.3A
SD3301BD	1.2A	1.9A
SD3301HD	2.7A	4.3A
Peak Pulsed Drain Current		8.0A

Maximum Power Dissipation

	$T_C = +100^\circ C$	$T_C = +25^\circ C$
HD, TO-39 Pkg.	6.0W	15W
BD, TO-92 Pkg.	1.2W	3.0W
AD, TO-237 Pkg.	1.7W	4.3W

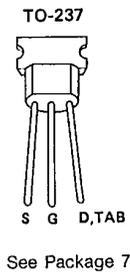
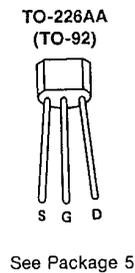
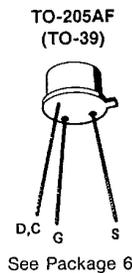
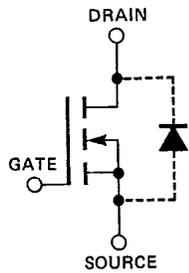
Linear Derating Factor

	Junction to Ambient ($mW/^\circ C$)	Junction to Case ($mW/^\circ C$)
HD, TO-39 Pkg.	8.0	120
BD, TO-92 Pkg.	3.2	24
AD, TO-237 Pkg.	4.8	34.4

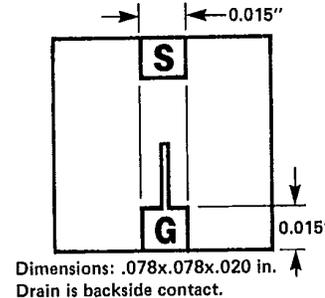
Operating Junction and Storage

Temperature Range	-55 to $+150^\circ C$
Lead Temperature (1/16" from mounting surface for 30 Sec)	$+260^\circ C$

PIN CONFIGURATIONS



CHIP CONFIGURATION





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ELECTRICAL CHARACTERISTICS (T_c = +25°C unless otherwise noted)

#	CHARACTERISTIC	SD3300			SD3301			UNIT	TEST CONDITIONS
		MIN	TYP	MAX	MIN	TYP	MAX		
1	BV _{DSS} Drain-Source Breakdown Voltage	100	125		60	90		V	I _D = 250μA, V _{GS} = 0
2	V _{GS(th)} Gate-Source Threshold Voltage	1.0		3.0	1.0		3.0	V	V _{DS} = V _{GS}
3		0.4			0.4				I _D = 250μA T _C = +125°C
4	I _{GSS} Gate-Body Leakage Current			100			100	nA	V _{GS} = 20V, V _{DS} = 0
5				200			200		T _C = +125°C
6				-100			-100		V _{GS} = -20V, V _{DS} = 0
7	I _{DSS} Drain-Source OFF Leakage Current			1.0				μA	V _{DS} = 80V, V _{GS} = 0
8				1000					T _C = +125°C
9							1.0		V _{DS} = 48V, V _{GS} = 0
10							1000		T _C = +125°C
11	I _{D(on)} ON Drain Current ⁽¹⁾	3.0			3.5			A	V _{DS} = 10V, V _{GS} = 10V
12	V _{DS(on)} Drain-Source ⁽¹⁾ ON Voltage			1.8				V	V _{GS} = 10V, I _D = 3.0A
13							1.4		V _{GS} = 10V, I _D = 3.5A
14	r _{DS(on)} Drain-Source ⁽¹⁾ ON Resistance			0.6			0.4	ohms	V _{GS} = 10V
15				1.08			0.72		I _D = 2.25A T _C = +125°C
16	g _{fs} Common-Source ⁽¹⁾ Forward Transcond.	1.0		3.0	1.0		3.0	S(Ω)	V _{DS} = 10V I _D = 2.25A f = 1KHz
17	C _{iss} Common-Source Input Capacitance			200			200	pF	V _{DS} = 25V, V _{GS} = 0 f = 1MHz
18	C _{rss} Common-Source Reverse Transfer Capacitance			25			25		
19	C _{OSS} Common-Source Output Capacitance			100			100		
20	t _{d(on)} Turn-ON Delay Time			15			15	nsec	V _{DD} = 34V R _L = 15 ohms R _G = 25 ohms V _{G(on)} = 10V
21	t _r Rise Time			25			25		
22	t _{d(off)} Turn-OFF Delay Time			25			25		
23	t _f Fall Time			20			20		
24	I _S Continuous Source Current ⁽¹⁾	3.0			3.5			A	
25	I _{SM} Peak Source Current ⁽¹⁾	8.0			8.0				
26	V _{SD} Source-Drain ⁽¹⁾ Forward Voltage			2.0				V	V _{GS} = 0 I _S = 3.0A
27							2.0		I _S = 3.5A

Note 1: Pulse Test 80μSec, 1% Duty Cycle

TYPICAL PERFORMANCE CHARACTERISTICS ($T_A = +25^\circ\text{C}$ unless otherwise specified)

